

High –Speed Switching Diode

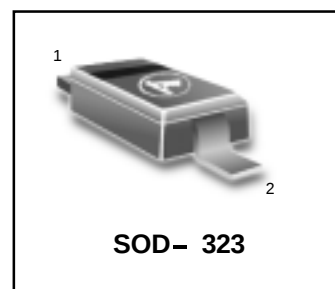
LMDL914T1

LMDL914T1

- Pb-Free Package is available.

ORDERING INFORMATION

Device	Package	Shipping
LMDL914T1	SOD-323	3000/Tape&Reel
LMDL914T1G (Pb-Free)	SOD-323	3000/Tape&Reel



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		1.57	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	150	$^\circ\text{C}$

**FR-4 Minimum Pad

DEVICE MARKING

LMDL914T1 = 5D

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_R = 100 \mu\text{Adc}$)	$V_{(BR)}$	100	—	Vdc
Reverse Voltage Leakage Current ($V_R = 20\text{Vdc}$)	I_R	—	25	nAdc
($V_R = 75\text{Vdc}$)		—	5.0	μAdc
Diode Voltage ($V_R = 0, f = 1.0\text{MHz}$)	C_T	—	4.0	pF
Forward Voltage ($I_F = 10 \text{mAdc}$)	V_F	—	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{mAdc}$) (Figure 1)	t_{rr}	—	4.0	ns

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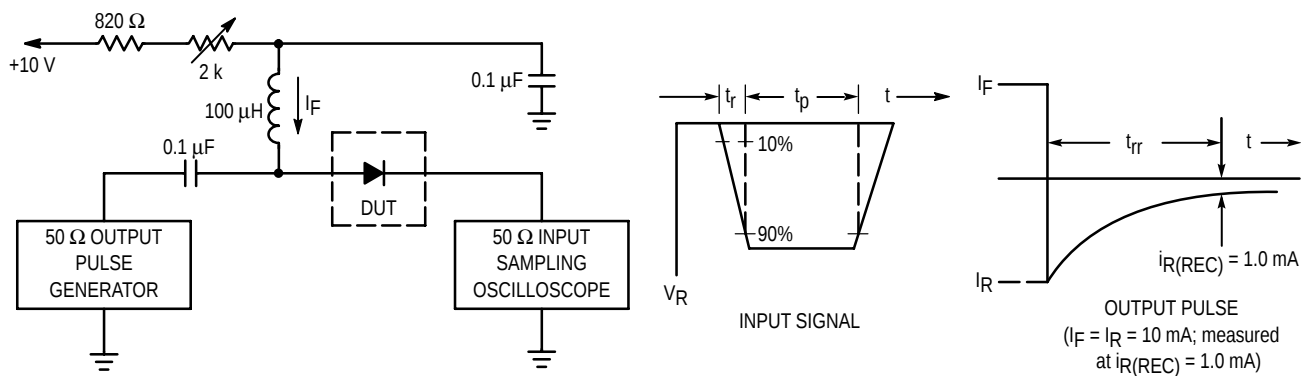


Figure 1. Recovery Time Equivalent Test Circuit

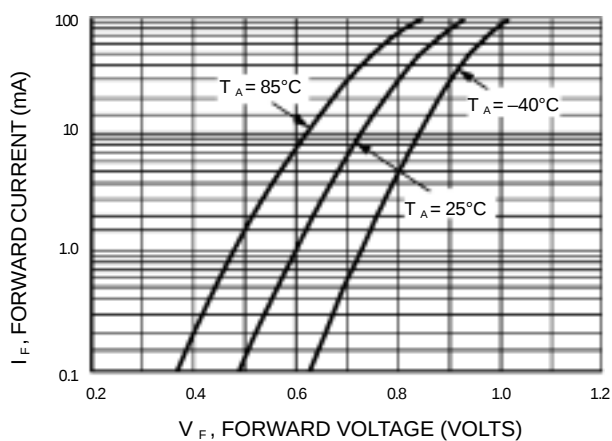


Figure 2. Forward Voltage

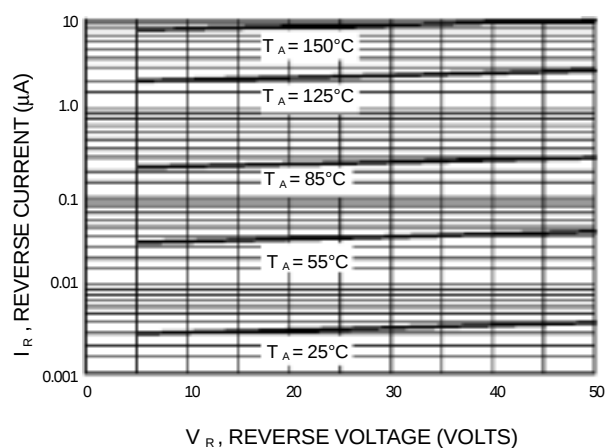


Figure 3. Leakage Current

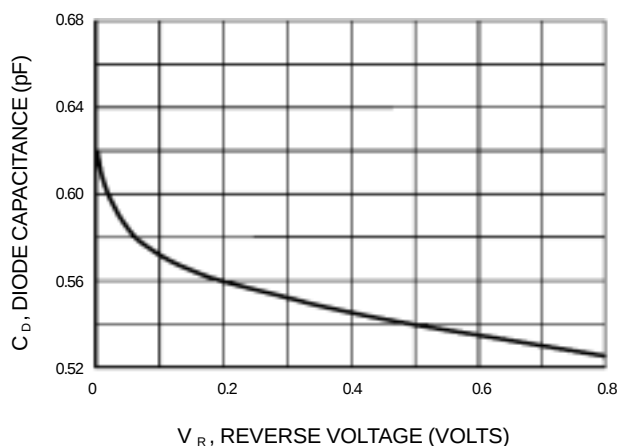
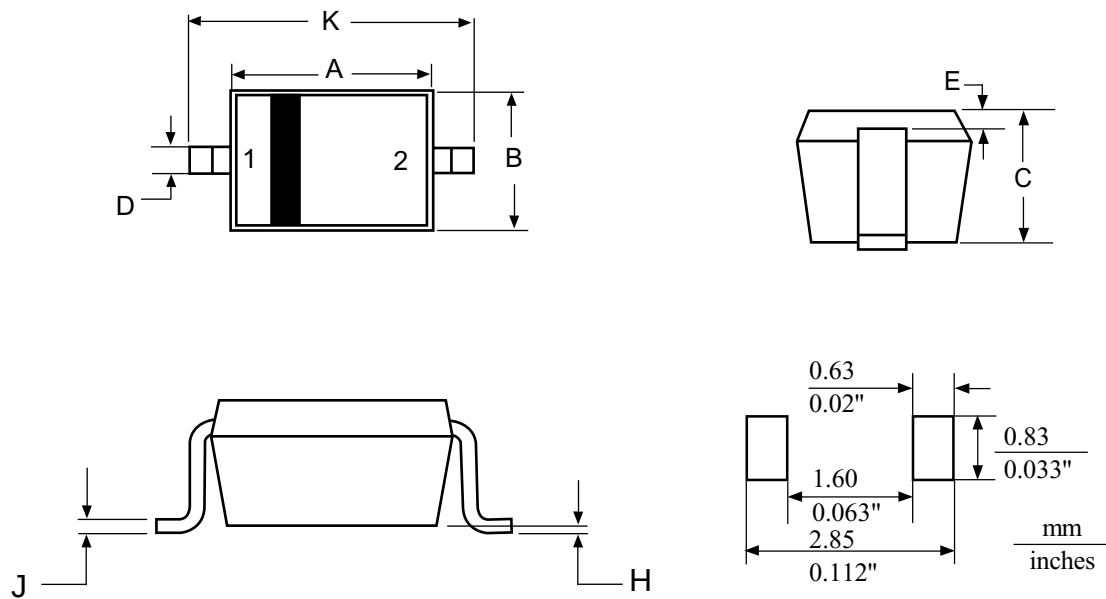


Figure 4. Capacitance

LMDL914T1
SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING
PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE
2:ANODE